



# **DUAL SURFACE MOUNT NPN/PNP TRANSISTORS (COMPLIMENTARY)**

This device contains two electrically-isolated complimentary pair (NPN and PNP) general-purpose transistors. This device is ideal for portable applications where board space is at a premium.

#### **FEATURES**

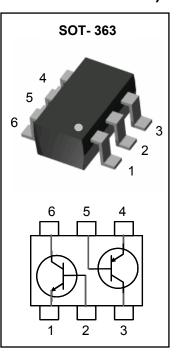
- Electrically-Isolated Complimentary Transistor Pairs
- Acqire quality system certificate: TS16949
- AEC-Q101 qualified
- Lead free in comply with EU RoHS 2002/95/EC directives.
- Green molding compound as per IEC61249 Std. . (Halogen Free)

### **APPLICATIONS**

- General Purpose Amplifier Applications
- Hand-Held Computers, PDAs

**Device Marking Code: 47P** 

### **MAXIMUM RATINGS - NPN**



 $T_J = 25$ °C Unless otherwise noted

Rating	Symbol	Value	Units
Collector-Base Voltage	$V_{CBO}$	50	V
Collector-Emitter Voltage	$V_{CEO}$	45	V
Emitter-Base Voltage Voltage	V <sub>EBO</sub>	6.0	V
Collector Current	I <sub>C</sub>	100	mA

### **MAXIMUM RATINGS - PNP**

 $T_J$  = 25°C Unless otherwise noted

Rating	Symbol	Value	Units
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-45	V
Emitter-Base Voltage Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current	I <sub>C</sub>	-100	mA

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P <sub>D</sub>	200	mW
Operating Junction Temperature Range	TJ	-55 to +150	°C
Storage Temperature Range	Tstg	-55 to +150	°C
Thermal Resistance, Junction to Ambient (Note 1)	R <sub>thja</sub>	556	°C/W

Note 1. FR-4 board 70 x 60 x 1mm with minimum recommended pad layout





# **NPN ELECTRICAL CHARACTERISTICS (Note 2)**

T<sub>J</sub> = 25°C Unless otherwise noted

Parameter	Symbol	Conditions	Min	Тур	Max	Units
Collector-Emitter Breakdown Voltage	€V <sub>(BR)CEO</sub>	I <sub>C</sub> = 10mA	45	-	-	V
Collector-Emitter Breakdown Voltage	V <sub>(BR)CES</sub>	I <sub>C</sub> = 10uA, V <sub>EB</sub> = 0	50	-	-	V
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 10uA	50	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I <sub>E</sub> = 1.0uA	6.0	-	-	V
Collector Cutoff Current	lan a	Van= 20V I == 0	-	-	15	nA
Collector Cutoff Current	ICBO	$I_{CBO}$ $V_{CB}=30V, I_{E}=0$ $T_{J}=150^{\circ}C$		-	5	uA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> = 5V, I <sub>C</sub> = 0	-	-	100	nA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = 5V, I c= 2.0mA	200	-	450	-
Callagtar Fraitter Caturation Valtage	VCE(SAT)	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0.5mA	-	-	0.1	V
Collector-Emitter Saturation Voltage		$I_C = 100 \text{mA}, I_B = 5 \text{mA}$	-	-	0.4	V
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0.5mA	-	0.75	-	V
Base-Emitter Voltage	$V_{BE}$	V <sub>CE</sub> = 5V, I c= 2.0mA	0.58	-	0.7	V
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = 5V, I c= 10mA f = 100MHz	100	-	-	MHz
Collector-Base Capacitance	Ссво	V <sub>CB</sub> = 10V, f =1.0MHz	-	-	1.5	pF
Emitter-Base Capacitance	Сево	V <sub>EB</sub> = 0.5V, f =1.0MHz	-	7	-	pF

# PNP ELECTRICAL CHARACTERISTICS (Note 2)

T = 25°C Unless otherwise noted

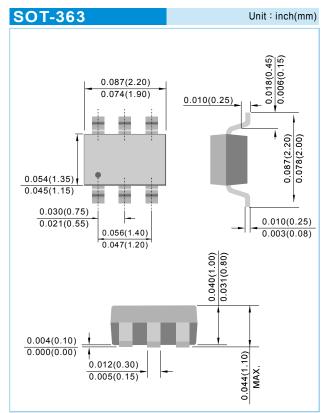
Parameter	Symbol	Conditions	Min	Тур	Max	Units
Collector-Emitter Breakdown Voltag	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -10mA	-45	-	-	V
Collector-Emitter Breakdown Voltage	V <sub>(BR)CES</sub>	I <sub>C</sub> = -10uA, V <sub>EB</sub> = 0	-50	-	-	V
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = -10uA	-50	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I <sub>E</sub> = -1.0uA	-5.0	-	-	V
Collector Cutoff Current	lana	Van= 20V L== 0	-	-	-15	nA
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> = -30V, I <sub>E</sub> = 0 T <sub>J</sub> =150°C	-	-	-4.0	uA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> = 0	-	-	-100	nA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = -5V, I c= -2.0mA	200	-	475	
Collector-Emitter Saturation Voltage	VOE(OAT)	$I_C = -10 \text{mA}, I_B = -0.5 \text{mA}$	-	-	-0.3	V
Collector-Emitter Saturation Voltage	VCE(SAT)	$I_C = -100 \text{mA}, I_B = -5 \text{mA}$	-	-	-0.65	V
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA	-	-0.7	-	\ \
Base-Emitter Voltage	V <sub>BE</sub>	V <sub>CE</sub> = -5V, I c= -2.0mA	-0.6	-	-0.75	V
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = -5V, I c= -10mA f = 100MHz	100	•	-	MHz
Collector-Base Capacitance	Ссво	V <sub>CB</sub> = -10V, f =1.0MHz	-	-	4.5	pF
Emitter-Base Capacitance	Сево	V <sub>EB</sub> = -0.5V, f =1.0MHz	-	11	-	pF

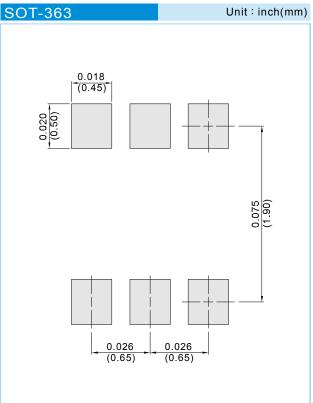
Note 2. Short duration test pulse used to minimize self-heating





### PACKAGE LAYOUT AND SUGGESTED PAD DIMENSIONS





### **ORDERING INFORMATION**

BC847BPN T/R7 - 3,000 units per 7 inch reel BC847BPN T/R13 -10,000 units per 13 inch reel





# **BC847BPN-AU**

# Part No\_packing code\_Version

BC847BPN-AU\_R1\_000A1 BC847BPN-AU\_R2\_000A1

# For example:



Packing Code XX			Version Code XXXXX			
Packing type	1 <sup>st</sup> Code	Packing size code	2 <sup>nd</sup> Code	HF or RoHS	1 <sup>st</sup> Code	2 <sup>nd</sup> ~5 <sup>th</sup> Code
Tape and Ammunition Box (T/B)	Α	N/A	0	HF	0	serial number
Tape and Reel (T/R)	R	7"	1	RoHS	1	serial number
Bulk Packing (B/P)	В	13"	2			
Tube Packing (T/P)	Т	26mm	X			
Tape and Reel (Right Oriented) (TRR)	S	52mm	Y			
Tape and Reel (Left Oriented) (TRL)	L	PANASERT T/B CATHODE UP (PBCU)	U			
FORMING	F	PANASERT T/B CATHODE DOWN (PBCD)	D			

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# **BC847BPN-AU**

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